

74LVC3G17

Triple non-inverting Schmitt trigger with 5 V tolerant input

Rev. 01 — 24 June 2004

Product data sheet

1. General description

The 74LVC3G17 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC3G17 provides three non-inverting buffers with Schmitt-trigger action. It is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-B exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V.
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- SOT505 and SOT765 package
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C.

3. Applications

- Wave and pulse shapers for highly noisy environments.

PHILIPS

4. Quick reference data

Table 1: Quick reference data

$GND = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{PHL} , t_{PLH}	propagation delay inputs nA to output nY	$V_{CC} = 1.8\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 1\text{ k}\Omega$	-	5.6	-	ns
		$V_{CC} = 2.5\text{ V}$; $C_L = 30\text{ pF}$; $R_L = 500\text{ }\Omega$	-	3.7	-	ns
		$V_{CC} = 2.7\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\text{ }\Omega$	-	3.8	-	ns
		$V_{CC} = 3.3\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\text{ }\Omega$	-	3.6	-	ns
		$V_{CC} = 5.0\text{ V}$; $C_L = 50\text{ pF}$; $R_L = 500\text{ }\Omega$	-	2.7	-	ns
C_I	input capacitance		-	3.5	-	pF
C_{PD}	power dissipation capacitance per buffer	$V_{CC} = 3.3\text{ V}$	[1] [2]	16.3	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

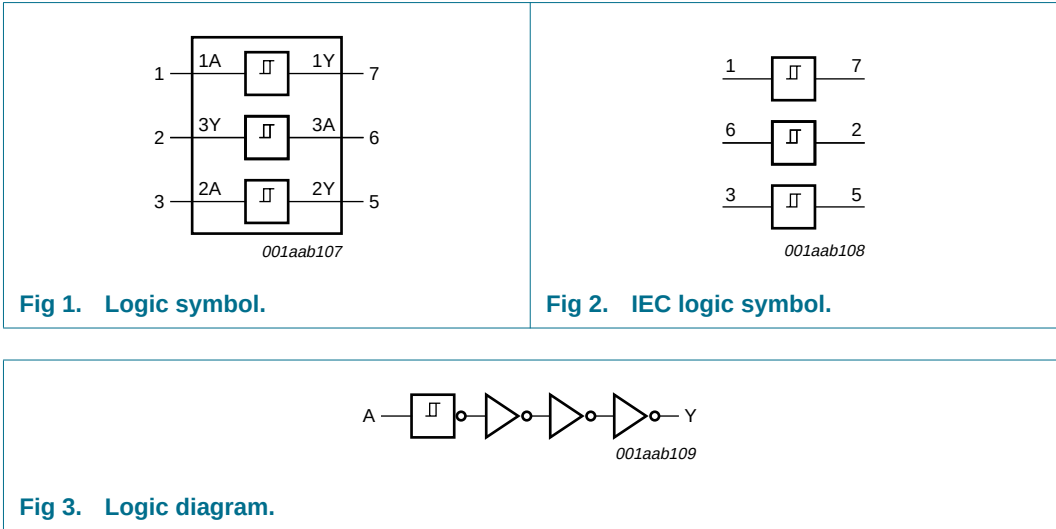
[2] The condition is $V_I = GND$ to V_{CC} .

5. Ordering information

Table 2: Ordering information

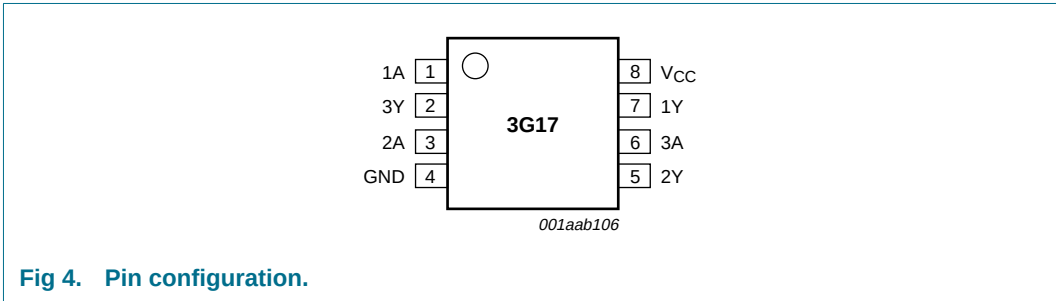
Type number	Package			
	Temperature range	Name	Description	Version
74LVC3G17DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC3G17DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3: Pin description		
Symbol	Pin	Description
1A	1	data input
3Y	2	data output
2A	3	data input
GND	4	ground (0 V)
2Y	5	data output
3A	6	data input
1Y	7	data output
V _{CC}	8	supply voltage

8. Functional description

8.1 Function table

Table 4: Function table ^[1]

Input	Output
nA	nY
L	L
H	H

[1] H = HIGH voltage level;
L = LOW voltage level.

9. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$ V	-	-50	mA
V_I	input voltage		^[1] -0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
V_O	output voltage	active mode	^[1] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	^[1] ^[2] -0.5	+6.5	V
I_O	output source or sink current	$V_O = 0$ V to V_{CC}	-	±50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		-	±100	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	power dissipation	$T_{amb} = -40$ °C to +125 °C	-	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

10. Recommended operating conditions

Table 6: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	operating ambient temperature		-40	-	+125	°C

11. Static characteristics

Table 7: Static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]						
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100\text{ }\mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	-	-	0.1	V
		$I_O = 4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	-	-	0.45	V
		$I_O = 8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.3	V
		$I_O = 12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	-	-	0.4	V
		$I_O = 24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.55	V
		$I_O = 32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	-	0.55	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100\text{ }\mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	1.2	-	-	V
		$I_O = -8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	1.9	-	-	V
		$I_O = -12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	2.2	-	-	V
		$I_O = -24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	2.3	-	-	V
		$I_O = -32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	3.8	-	-	V
I_{LI}	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 5.5\text{ V}$	-	± 0.1	± 5	μA
I_{off}	power off leakage current	V_I or $V_O = 5.5\text{ V}$; $V_{CC} = 0\text{ V}$	-	± 0.1	± 10	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	0.1	10	μA
ΔI_{CC}	additional quiescent supply current per pin	$V_I = V_{CC} - 0.6\text{ V}$; $I_O = 0\text{ A}$; $V_{CC} = 2.3\text{ V to }5.5\text{ V}$	-	5	500	μA
C_I	input capacitance		-	3.5	-	pF
$T_{amb} = -40\text{ °C to }+125\text{ °C}$						
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100\text{ }\mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	-	-	0.1	V
		$I_O = 4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	-	-	0.70	V
		$I_O = 8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.45	V
		$I_O = 12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	-	-	0.60	V
		$I_O = 24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.80	V
		$I_O = 32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	-	0.80	V

Table 7: Static characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100\ \mu\text{A}$; $V_{CC} = 1.65\ \text{V}$ to $5.5\ \text{V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -4\ \text{mA}$; $V_{CC} = 1.65\ \text{V}$	0.95	-	-	V
		$I_O = -8\ \text{mA}$; $V_{CC} = 2.3\ \text{V}$	1.7	-	-	V
		$I_O = -12\ \text{mA}$; $V_{CC} = 2.7\ \text{V}$	1.9	-	-	V
		$I_O = -24\ \text{mA}$; $V_{CC} = 3.0\ \text{V}$	2.0	-	-	V
		$I_O = -32\ \text{mA}$; $V_{CC} = 4.5\ \text{V}$	3.4	-	-	V
I_{LI}	input leakage current	$V_I = 5.5\ \text{V}$ or GND; $V_{CC} = 5.5\ \text{V}$	-	-	± 20	μA
I_{off}	power off leakage current	V_I or $V_O = 5.5\ \text{V}$; $V_{CC} = 0\ \text{V}$	-	-	± 20	μA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0\ \text{A}$; $V_{CC} = 5.5\ \text{V}$	-	-	40	μA
ΔI_{CC}	additional quiescent supply current per pin	$V_I = V_{CC} - 0.6\ \text{V}$; $I_O = 0\ \text{A}$; $V_{CC} = 2.3\ \text{V}$ to $5.5\ \text{V}$	-	-	5000	μA

[1] All typical values are measured at $V_{CC} = 3.3\ \text{V}$ and $T_{amb} = 25\ ^\circ\text{C}$.

12. Dynamic characteristics

Table 8: Dynamic characteristics

GND = 0 V.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\ ^\circ\text{C}$ to $+85\ ^\circ\text{C}$ [1]						
t_{PHL} , t_{PLH}	propagation delay nA to nY	see Figure 5 and 6				
		$V_{CC} = 1.65\ \text{V}$ to $1.95\ \text{V}$	1.5	5.6	10.5	ns
		$V_{CC} = 2.3\ \text{V}$ to $2.7\ \text{V}$	1.0	3.7	6.5	ns
		$V_{CC} = 2.7\ \text{V}$	1.0	3.8	6.5	ns
		$V_{CC} = 3.0\ \text{V}$ to $3.6\ \text{V}$	1.0	3.6	5.7	ns
		$V_{CC} = 4.5\ \text{V}$ to $5.5\ \text{V}$	1.0	2.7	4.3	ns
C_{PD}	power dissipation capacitance per buffer	$V_{CC} = 3.3\ \text{V}$	[2] [3] -	16.3	-	pF

Table 8: Dynamic characteristics ...continued

GND = 0 V.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{\text{amb}} = -40\text{ }^{\circ}\text{C to } +125\text{ }^{\circ}\text{C}$						
$t_{\text{PHL}}, t_{\text{PLH}}$	propagation delay nA to nY	see Figure 5 and 6				
		$V_{\text{CC}} = 1.65\text{ V to } 1.95\text{ V}$	1.5	-	13.1	ns
		$V_{\text{CC}} = 2.3\text{ V to } 2.7\text{ V}$	1.0	-	8.5	ns
		$V_{\text{CC}} = 2.7\text{ V}$	1.0	-	8.5	ns
		$V_{\text{CC}} = 3.0\text{ V to } 3.6\text{ V}$	1.0	-	7.1	ns
		$V_{\text{CC}} = 4.5\text{ V to } 5.5\text{ V}$	1.0	-	5.4	ns

[1] All typical values are measured at nominal V_{CC} and $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$.

[2] C_{PD} is used to determine the dynamic power dissipation (P_{D} in μW).

$P_{\text{D}} = C_{\text{PD}} \times V_{\text{CC}}^2 \times f_{\text{i}} \times N + \sum (C_{\text{L}} \times V_{\text{CC}}^2 \times f_{\text{o}})$ where:

f_{i} = input frequency in MHz;

f_{o} = output frequency in MHz;

C_{L} = output load capacitance in pF;

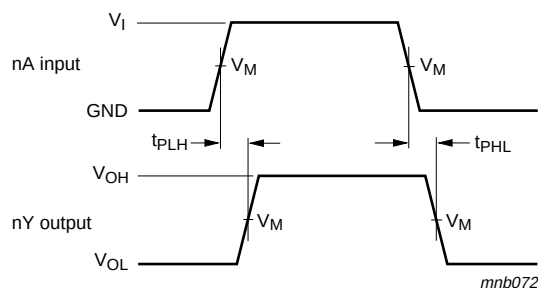
V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\sum (C_{\text{L}} \times V_{\text{CC}}^2 \times f_{\text{o}})$ = sum of outputs.

[3] The condition is $V_{\text{I}} = \text{GND to } V_{\text{CC}}$.

13. Waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 5. The input (nA) to output (nY) propagation delays.

Table 9: Measurement points

Supply voltage	Input		Output
V_{CC}	V_{M}	V_{I}	V_{M}
1.65 V to 1.95 V	$0.5 \times V_{\text{CC}}$	V_{CC}	$0.5 \times V_{\text{CC}}$
2.3 V to 2.7 V	$0.5 \times V_{\text{CC}}$	V_{CC}	$0.5 \times V_{\text{CC}}$
2.7 V	1.5 V	2.7 V	1.5 V
3.0 V to 3.6 V	1.5 V	2.7 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{\text{CC}}$	V_{CC}	$0.5 \times V_{\text{CC}}$

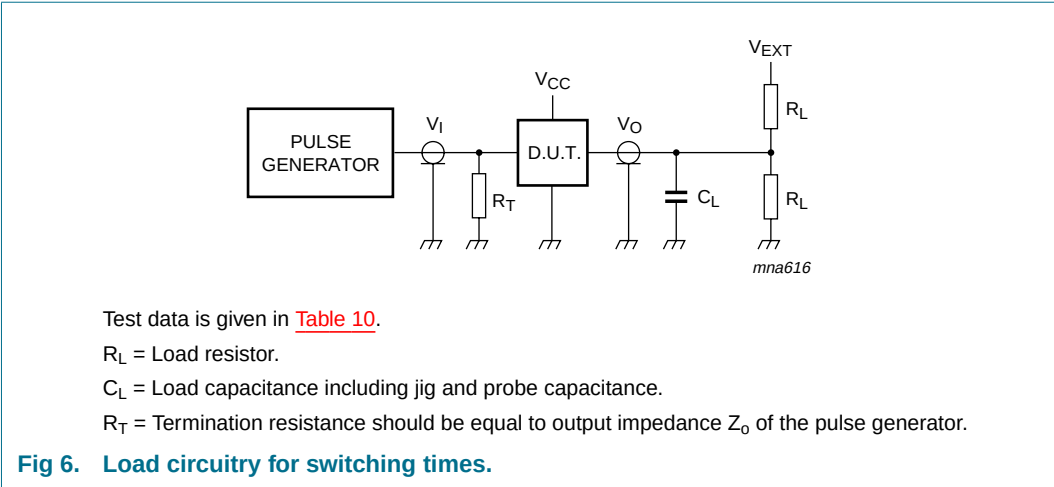


Table 10: Test data

Supply voltage	Input	Load			V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open	GND	$2 \times V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

14. Transfer characteristics

Table 11: Transfer characteristics

Voltages are referenced to GND (ground = 0 V).

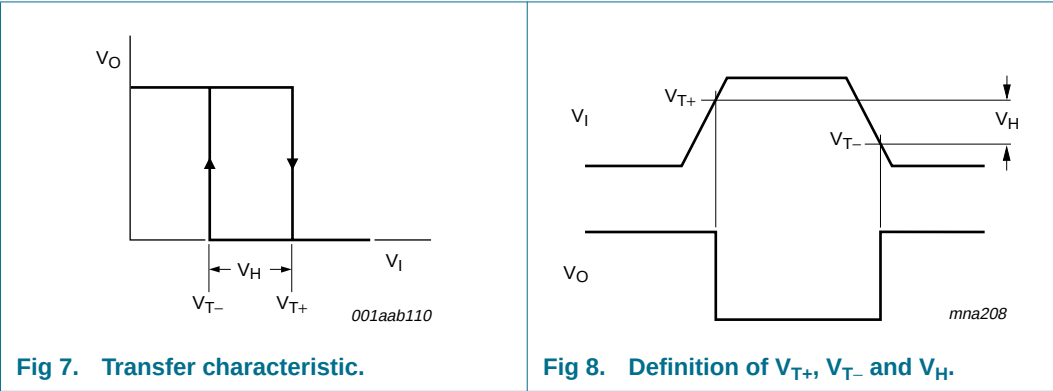
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ }^{\circ}\text{C to }+85\text{ }^{\circ}\text{C}$ [1]						
V_{T+}	positive-going threshold	see Figure 7 and 8				
		$V_{CC} = 1.8\text{ V}$	0.70	1.10	1.50	V
		$V_{CC} = 2.3\text{ V}$	1.00	1.40	1.80	V
		$V_{CC} = 3.0\text{ V}$	1.30	1.76	2.20	V
		$V_{CC} = 4.5\text{ V}$	1.90	2.47	3.10	V
		$V_{CC} = 5.5\text{ V}$	2.20	2.91	3.60	V
V_{T-}	negative-going threshold	see Figure 7 and 8				
		$V_{CC} = 1.8\text{ V}$	0.25	0.61	0.90	V
		$V_{CC} = 2.3\text{ V}$	0.40	0.80	1.15	V
		$V_{CC} = 3.0\text{ V}$	0.60	1.04	1.50	V
		$V_{CC} = 4.5\text{ V}$	1.00	1.55	2.00	V
		$V_{CC} = 5.5\text{ V}$	1.20	1.86	2.30	V

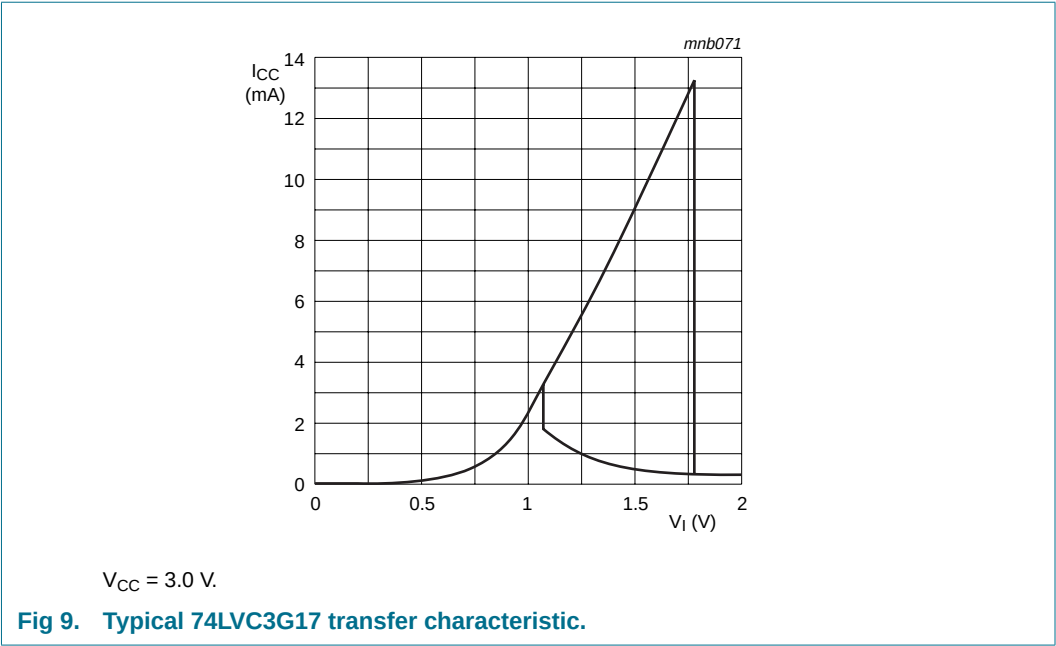
Table 11: Transfer characteristics ...continued
Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _H	hysteresis (V _{T+} – V _{T–})	see Figure 7 , 8 and 9				
		V _{CC} = 1.8 V	0.15	0.49	1.00	V
		V _{CC} = 2.3 V	0.25	0.60	1.10	V
		V _{CC} = 3.0 V	0.40	0.73	1.20	V
		V _{CC} = 4.5 V	0.60	0.92	1.50	V
		V _{CC} = 5.5 V	0.70	1.02	1.70	V
T _{amb} = –40 °C to +125 °C						
V _{T+}	positive-going threshold	see Figure 7 and 8				
		V _{CC} = 1.8 V	0.70	-	1.70	V
		V _{CC} = 2.3 V	1.00	-	2.00	V
		V _{CC} = 3.0 V	1.30	-	2.40	V
		V _{CC} = 4.5 V	1.90	-	3.30	V
		V _{CC} = 5.5 V	2.20	-	3.80	V
V _{T–}	negative-going threshold	see Figure 7 and 8				
		V _{CC} = 1.8 V	0.25	-	1.10	V
		V _{CC} = 2.3 V	0.40	-	1.35	V
		V _{CC} = 3.0 V	0.60	-	1.70	V
		V _{CC} = 4.5 V	1.00	-	2.20	V
		V _{CC} = 5.5 V	1.20	-	2.50	V
V _H	hysteresis (V _{T+} – V _{T–})	see Figure 7 , 8 and 9				
		V _{CC} = 1.8 V	0.15	-	1.20	V
		V _{CC} = 2.3 V	0.25	-	1.30	V
		V _{CC} = 3.0 V	0.40	-	1.40	V
		V _{CC} = 4.5 V	0.60	-	1.70	V
		V _{CC} = 5.5 V	0.70	-	1.90	V

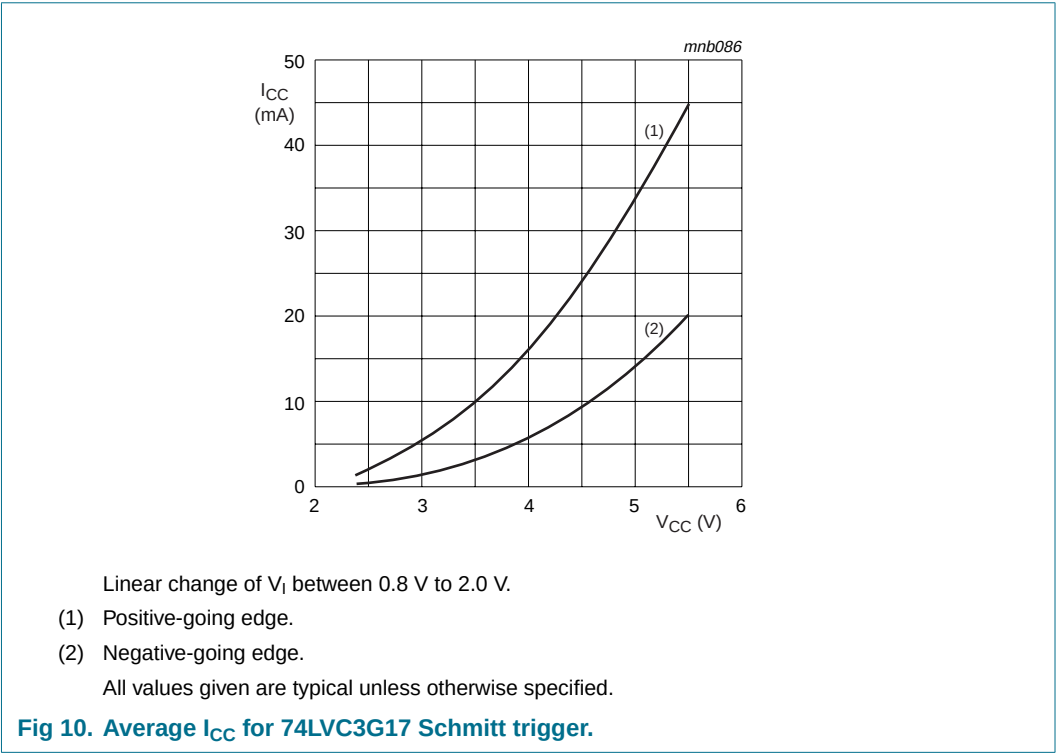
[1] All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

15. Waveforms transfer characteristics





16. Application information



17. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

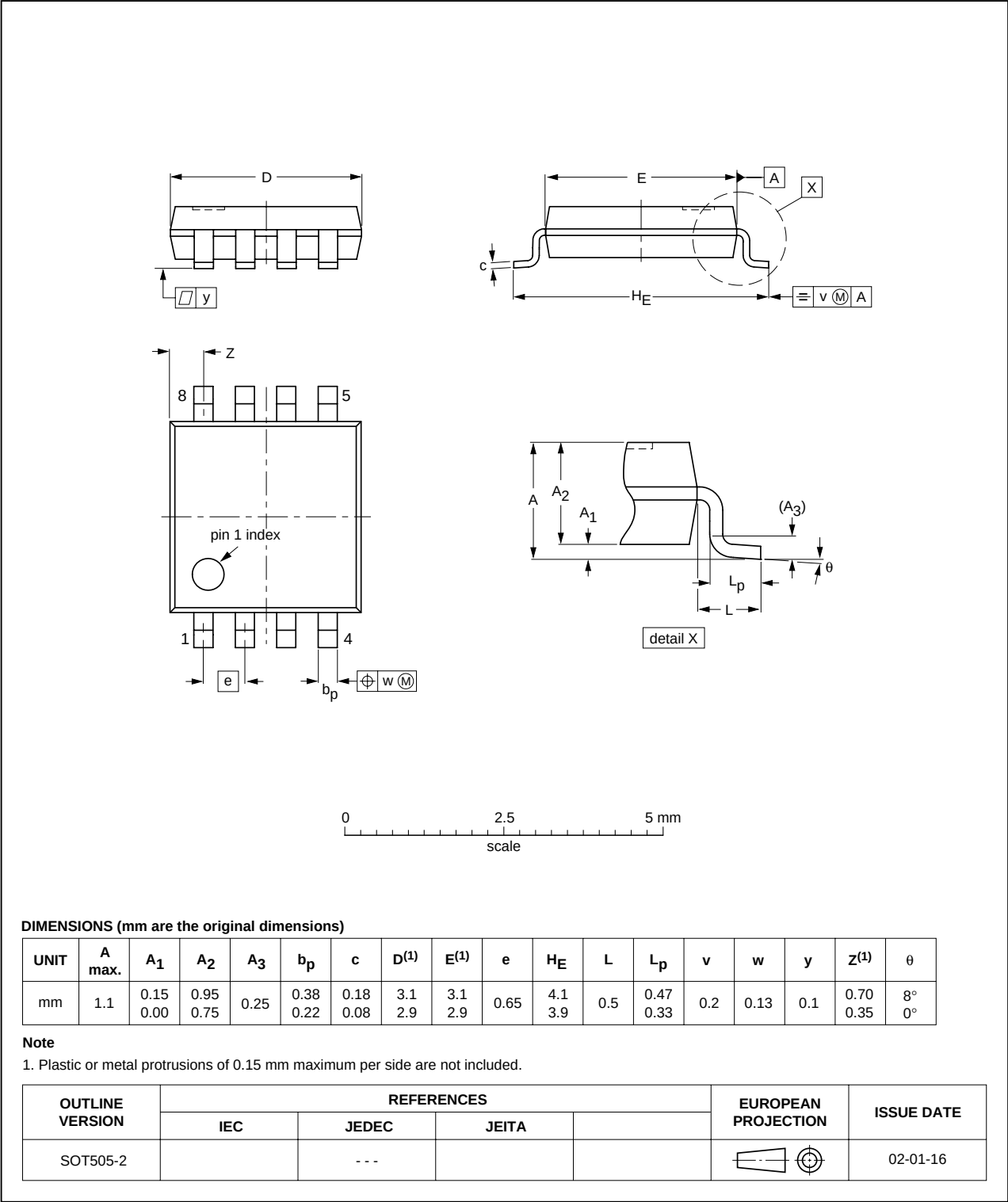
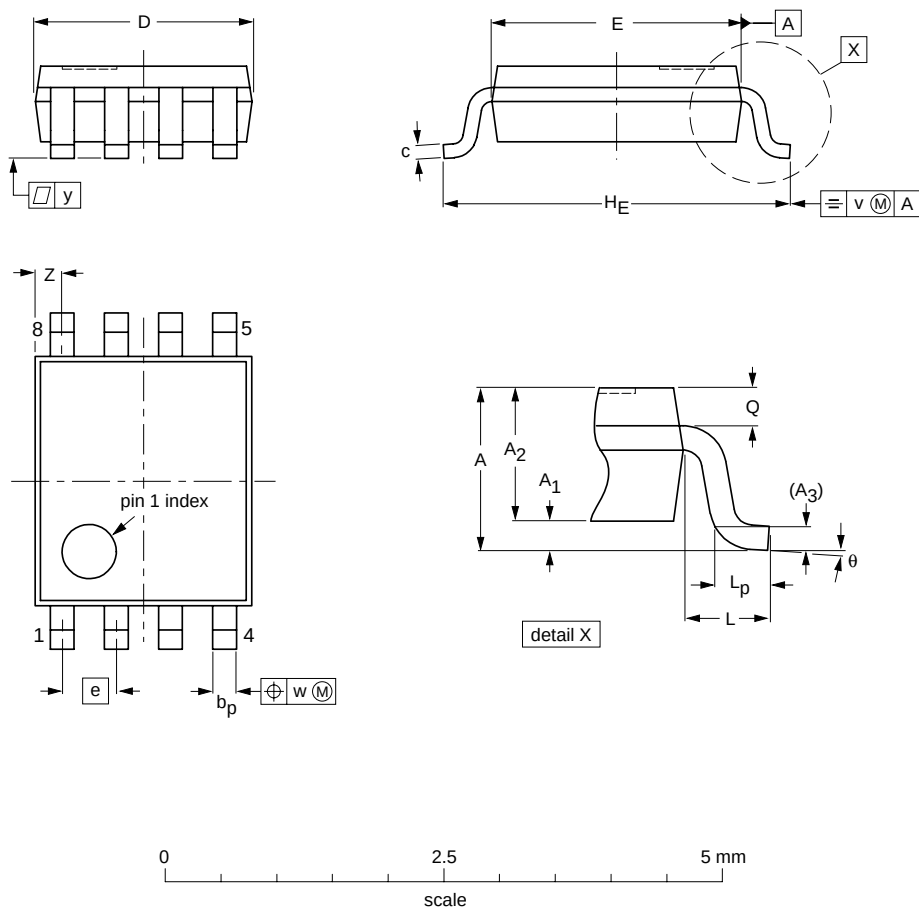


Fig 11. Package outline TSSOP8.

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- Notes
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 12. Package outline VSSOP8.

18. Revision history

Table 12: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
74LVC3G17_1	20040624	Product data	-	9397 750 13332	-

19. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

20. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

21. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

22. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

23. Contents

1	General description	1
2	Features	1
3	Applications	1
4	Quick reference data	2
5	Ordering information	2
6	Functional diagram	3
7	Pinning information	3
7.1	Pinning	3
7.2	Pin description	3
8	Functional description	4
8.1	Function table	4
9	Limiting values	4
10	Recommended operating conditions	4
11	Static characteristics	5
12	Dynamic characteristics	6
13	Waveforms	7
14	Transfer characteristics	8
15	Waveforms transfer characteristics	9
16	Application information	10
17	Package outline	11
18	Revision history	13
19	Data sheet status	14
20	Definitions	14
21	Disclaimers	14
22	Contact information	14



© Koninklijke Philips Electronics N.V. 2004

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 24 June 2004
Document order number: 9397 750 13332

Published in The Netherlands